**Product data sheet** 

# 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006-3 (SOT883) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Very fast switching
- ElectroStatic Discharge (ESD) protection: 2 kV HBM
- Leadless ultra small SMD plastic package: 1.0 x 0.6 x 0.48 mm

## 3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	20	V
V <sub>GS</sub>	gate-source voltage			-8	-	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-	1.2	Α
Static characte	Static characteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 4.5 V; $I_D$ = 1.2 A; $T_j$ = 25 °C		-	270	320	mΩ

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.





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# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	1	D I
2	S	source	2 🔲 📗 3	
3	D	drain	Transparent top view  DFN1006-3 (SOT883)	G S 017aaa255

# 6. Ordering information

Table 3. Ordering information

Type number	Package	ge					
	Name	Description	Version				
PMZ290UNE2	DFN1006-3	DFN1006-3: leadless ultra small plastic package; 3 solder lands	SOT883				

# 7. Marking

Table 4. Marking codes

Type number	Marking code
PMZ290UNE2	SC

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### 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	20	V
$V_{GS}$	gate-source voltage			-8	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	1.2	Α
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	0.8	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10$ μs		-	4	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	350	mW
			[1]	-	715	mW
		T <sub>sp</sub> = 25 °C		-	5430	mW
T <sub>j</sub>	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drain o	liode				,	
Is	source current	T <sub>amb</sub> = 25 °C	[1]	-	0.7	Α

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

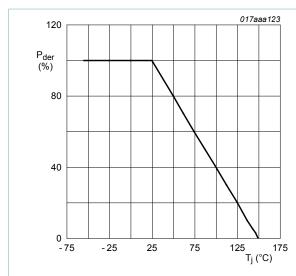


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

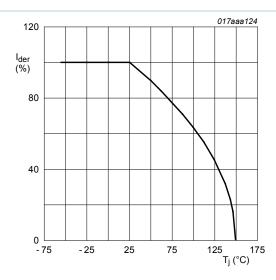


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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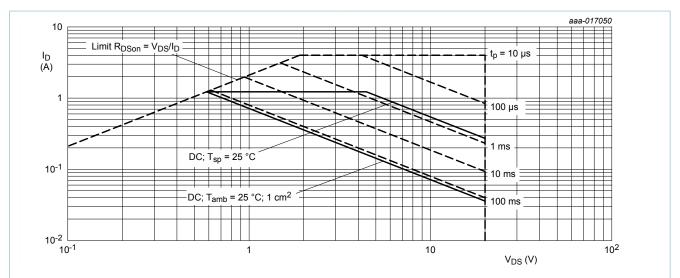


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
fror	thermal resistance	in free air	[1]	-	315	360	K/W
	from junction to ambient		<u>[2]</u>	-	150	175	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	20	23	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.

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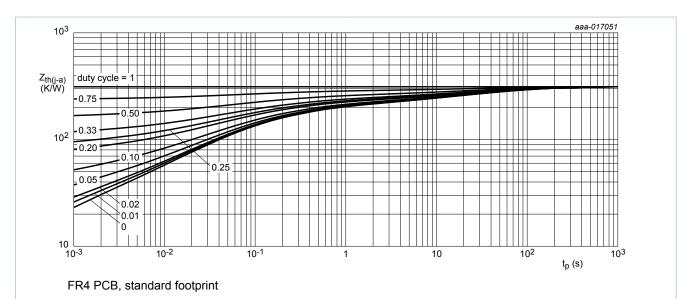


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

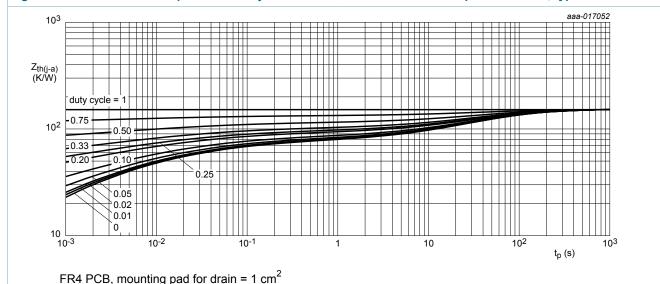


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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### 10. Characteristics

Table 7 Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics		'			
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D$ = 250 $\mu$ A; $V_{GS}$ = 0 V; $T_j$ = 25 °C	20	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D$ = 250 $\mu$ A; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C	0.45	0.7	0.95	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	5	μΑ
		V <sub>GS</sub> = -8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-5	μΑ
		V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μΑ
		$V_{GS}$ = -4.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-1	μΑ
		$V_{GS}$ = 2.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	100	nA
		$V_{GS}$ = -2.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-100	nA
Doon	drain-source on-state resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 1.2 A; T <sub>j</sub> = 25 °C	-	270	320	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 1.2 A; T <sub>j</sub> = 150 °C	-	400	475	mΩ
		$V_{GS}$ = 2.5 V; $I_D$ = 1.0 A; $T_j$ = 25 °C	-	360	480	mΩ
		V <sub>GS</sub> = 1.8 V; I <sub>D</sub> = 0.12 A; T <sub>j</sub> = 25 °C	-	470	680	mΩ
		V <sub>GS</sub> = 1.5 V; I <sub>D</sub> = 0.01 A; T <sub>j</sub> = 25 °C	-	600	1190	mΩ
9fs	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 1.23 \text{ A}; T_j = 25 \text{ °C}$	-	1.9	-	S
Dynamic cl	haracteristics					
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = 10 V; $I_{D}$ = 1.0 A; $V_{GS}$ = 4.5 V;	-	0.8	1.4	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C	-	0.1	-	nC
$Q_{GD}$	gate-drain charge		-	0.2	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	46	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	9.6	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	7.7	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 10 V; $I_D$ = 1.0 A; $V_{GS}$ = 4.5 V;	-	6	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega$ ; $T_j = 25 °C$	-	10	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	11	-	ns
t <sub>f</sub>	fall time		-	4	-	ns
Source-dra	in diode	ı		1		1
$V_{SD}$	source-drain voltage	$I_S = 0.7 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.9	1.2	V

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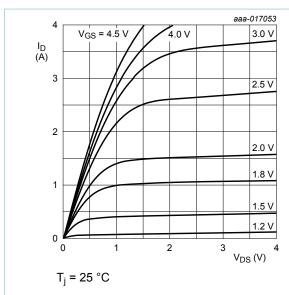
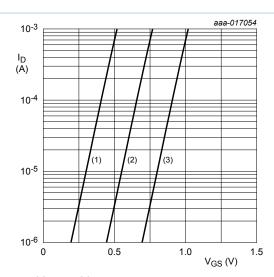


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



 $V_{DS} = 5 V$ 

T<sub>i</sub> = 25 °C

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage

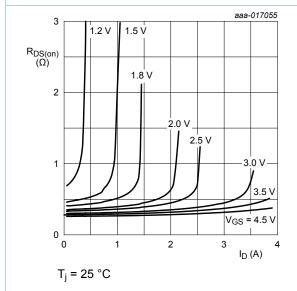


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

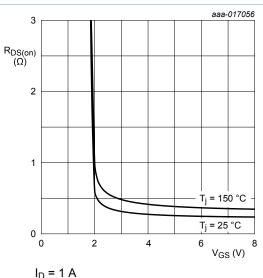


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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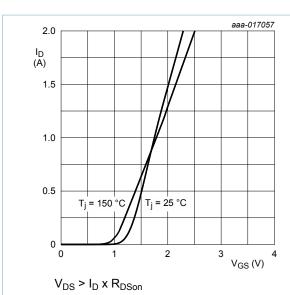


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

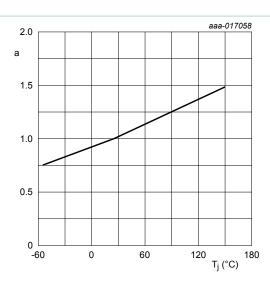
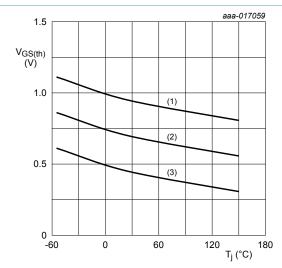


Fig. 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values

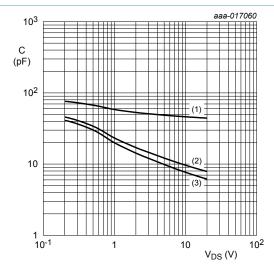
$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



 $I_D = 250 \mu A; V_{DS} = V_{GS}$ 

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 12. Gate-source threshold voltage as a function of ambient temperature

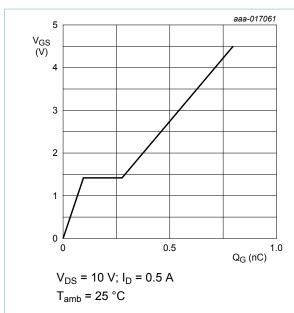


 $f = 1 MHz; V_{GS} = 0 V$ 

- (1) C<sub>iss</sub>
- (2) C<sub>oss</sub>
- (3) C<sub>rss</sub>

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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V<sub>GS</sub>(pl)
V<sub>GS</sub>(th)
V<sub>GS</sub>
Q<sub>GS1</sub> Q<sub>GS2</sub>
Q<sub>GG</sub>(tot)
003aaa508

Fig. 15. Gate charge waveform definitions

Fig. 14. Gate-source voltage as a function of gate charge; typical values

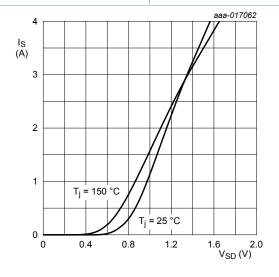
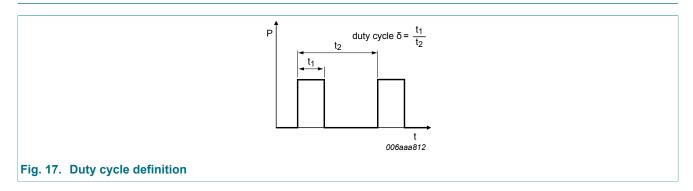


Fig. 16. Source current as a function of source-drain voltage; typical values

 $V_{GS} = 0 V$ 

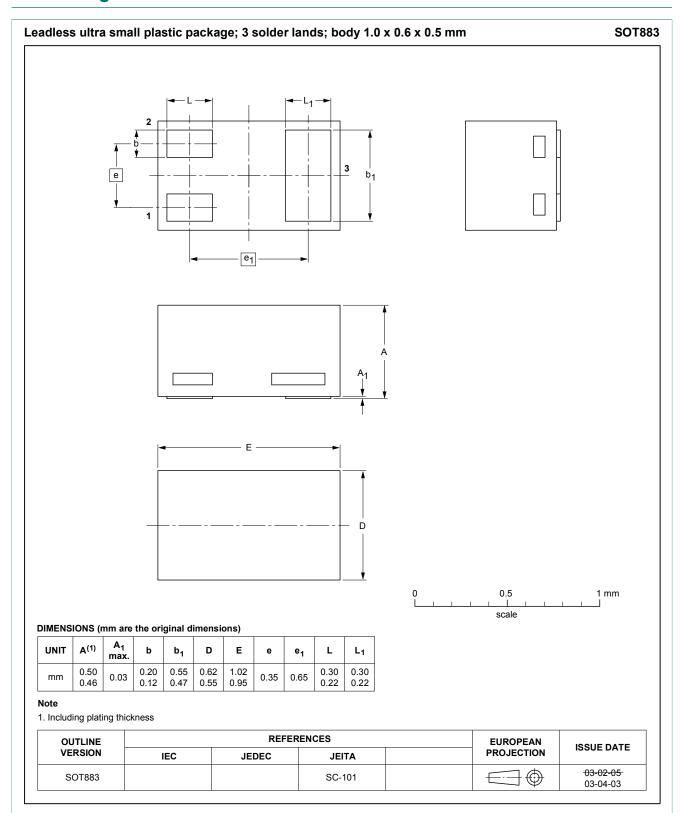
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# 11. Test information



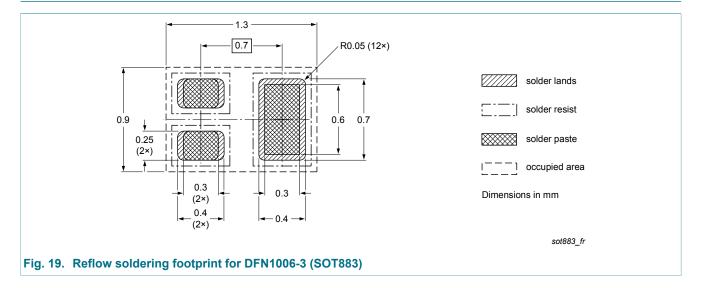
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### 12. Package outline



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# 13. Soldering



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# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMZ290UNE2 v.1	20150324	Product data sheet	-	-

#### 20 V, N-channel Trench MOSFET

### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
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